Abstracts

Multigigahertz Monolithic GaAs Optoelectronic Receivers Using 0.2 µm Gate-Length MESFETs

R.H. Walden, W.W. Hooper, C.S. Chou, C. Ngo, R. WongQuen, R.A. Metzger, F. Williams, L.E. Larson and R. Blumgold. "Multigigahertz Monolithic GaAs Optoelectronic Receivers Using 0.2 µm Gate-Length MESFETs." 1991 MTT-S International Microwave Symposium Digest 91.2 (1991 Vol. II [MWSYM]): 491-494.

Two GaAs optical receiver front-ends are reported. Each consists of an MSM photodetector and a tranaresistance amplifier that drives a 50 Omega load. One amplifier has a measured analog bandwidth of 6.5 GHz and the other 4.5 GHz. The transresistance-bandwidth product for both is a very high 2.1 THz-Omega.

❑ Return to main document.